

HA5023/883

Dual 125MHz Video Current Feedback Amplifier

January 1995

Features

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- Wide Unity Gain Bandwidth 125MHz
- Slew Rate 475V/µs
- Differential Phase 0.03 Deg.
- Supply Current (per Amplifier)7.5mA
- Crosstalk Rejection at 10MHz.....-60dB
- Guaranteed Specifications at ±5V Supplies

Applications

- Video Gain Block
- Video Distribution Amplifier/RGB Amplifier
- Flash A/D Driver
- **Current to Voltage Converter**
- Radar and Imaging Systems
- Medical Imaging

Description

The HA5023/883 is a dual version of the popular Intersil HA-5020/883 except that it does not have an enable function. It features wide bandwidth and high slew rate, and is optimized for video applications and gains between 1 and 10. It is a current feedback amplifier and thus yields less bandwidth degradation at high closed loop gains than voltage feedback amplifiers.

The low differential gain and phase, 0.1dB gain flatness, and ability to drive two back terminated 75Ω cables, make this amplifier ideal for demanding video applications.

The current feedback design allows the user to take advantage of the amplifier's bandwidth dependency on the feedback resistor. By reducing R_F, the bandwidth can be increased to compensate for decreases at higher closed loop gains or heavy output loads.

Ordering Information

PART NUMBER	TEMPERATURE RANGE	PACKAGE
HA5023MJ/883	-55°C to +125°C	8 Lead CerDIP

Pinout



CAUTION: These devices are sensitive to electrostatic discharge; follow proper IC Handling Procedures. 1-888-INTERSIL or 321-724-7143 | Intersil (and design) is a trademark of Intersil Americas Inc. Copyright © Intersil Americas Inc. 2002. All Rights Reserved

Absolute Maximum Ratings

Voltage Between V+ and V	36V
Differential Input Voltage	10V
Voltage at Either Input Terminal	V+ to V-
Output Current Fully Short Circu	it Protected
Junction Temperature	+175°C
ESD Rating	<2000V
Storage Temperature Range65°C ≤ T	_A ≤ +150°C
Lead Temperature (Soldering 10s)	+300°C

Thermal Information

Thermal Resistance CerDIP Package	θ _{JA} 115⁰C/W	θ _{JC} 28°C/W
Maximum Package Power Dissipation at -	+75°C	
CerDIP Package		0.87W
Package Power Dissipation Derating Fact	or above +75	οC
CerDIP Package		8.7mW/ºC

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Operating Conditions

Operating Supply Voltage (±V _S)	±5V to ±15V	V _{INCM} ≤ 1/2(V+ - V-)	
Operating Temperature Range55°C	≤ T _A ≤ +125°C	R _L Š≥ 50Ω	$R_F = 1k\Omega$

			GROUPA		LIN	IITS	
PARAMETERS	SYMBOL	CONDITIONS	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Input Offset Voltage	V _{IO}	$V_{CM} = 0V$	1	+25°C	-3	3	mV
			2, 3	+125°C, -55°C	-5	5	mV
Common Mode	CMRR	$\Delta V_{CM} = \pm 2.5 V$	1	+25°C	53	-	dB
Rejection Ratio		V+ = 2.5V, V- = -7.5V V+ = 7.5V, V- = -2.5V	2	+125°C	38	-	dB
		$\begin{array}{l} \Delta V_{CM} = \pm 2.25 V \\ V+ = 2.75 V, \ V- = -7.25 V \\ V+ = 7.25 V, \ V- = -2.75 V \end{array}$	3	-55°C	38	-	dB
Power Supply	PSRR	$\Delta V_{SUP} = \pm 1.5 V$	1	+25°C	60	-	dB
Rejection Ratio		V+ = 6.5V, V- = -5V V+ = 3.5V, V- = -5V	2, 3	+125°C, -55°C	55	-	dB
Delta Input Offset	ΔV_{IO}	ΔV_{IO} $V_{CM} = 0$		+25°C	-	3.5	mV
Voltage Between Channels			2,3	+125°C, -55°C	-	3.5	mV
Non-Inverting Input	n-Inverting Input I _{BSP}		1	+25°C	-8	8	μA
(+IN) Current		2, 3	+125°C, -55°C	-20	20	μA	
+IN Current Common Cl	CMSIBP	$\Delta V_{CM} = \pm 2.5 V$	1	+25°C	-	0.15	μ A /V
Mode Sensitivity		V+ = 2.5V, V- = -7.5V V+ = 7.5V, V- = -2.5V	2	+125°C	-	2.0	μ A /V
		$\begin{array}{l} \Delta V_{CM} = \pm 2.25 V \\ V+ = 2.75 V, \ V- = -7.25 V \\ V+ = 7.25 V, \ V- = -2.75 V \end{array}$	3	-55°C	-	2.0	μ Α/V
∆Inverting Input (-IN)	ΔI_{BSN}	ΔI_{BSN} $V_{CM} = 0$	1	+25°C	-15	15	μA
Current Between Channels			2, 3	+125°C, -55°C	-30	30	μA
Inverting Input (-IN)	I _{BSN}	$V_{CM} = 0V$	1	+25°C	-12	12	μA
Current			2, 3	+125°C, -55°C	-30	30	μA
-IN Current Common	CMS _{IBN}	$\Delta V_{CM} = \pm 2.5 V$	1	+25°C	-	0.4	μA/V
wode Sensitivity		V+ = 2.5V, V- = -7.5V V+ = 7.5V, V- = -2.5V	2	+125°C	-	5	μ A /V
		$\Delta V_{CM} = \pm 2.25V$ V+ = 2.75V, V- = -7.25V V+ = 7.25V, V- = -2.75V	3	-55°C	-	5	μ Α /V

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS $\pm \pm 5V$, $A_V = \pm 1$, $B_E = 1k\Omega$, $B_{SOURCE} = 0\Omega$, $B_L = 400\Omega$, $V_{OUT} = 0V$, Unless Ot

Specifications HA5023/883

			GROUP A		LIN	NITS	
PARAMETERS	SYMBOL	CONDITIONS	SUBGROUPS	TEMPERATURE	MIN	МАХ	UNITS
-IN Current Power	$PSS_{IBN} \Delta V_{SUP} = \pm 1.5 V$		1	+25°C	-	0.2	μA/V
Supply Sensitivity		V+ = 6.5V, V- = -5V V+ = 3.5V, V- = -5V	2, 3	+125°C, -55°C	-	0.5	μA/V
+IN Current Power	PSS _{IBP}	$\Delta V_{SUP} = \pm 1.5V$	1	+25°C	-	0.1	μA/V
Supply Sensitivity		V+ = 6.5V, V- = -5V V+ = 3.5V, V- = -5V	2, 3	+125°C, -55°C	-	0.3	μA/V
Output Voltage	V _{OP}	$A_V = +1$ $V_{IN} = -3V$	1	+25°C	2.5	-	V
Swing		$R_{L} = 150\Omega V_{IN} = -3V$	2, 3	+125°C, -55°C	2.5	-	V
	V _{ON}	$A_V = +1$ $V_{IN} = +3V$	1	+25°C	-	-2.5	V
		$R_{L} = 150\Omega V_{IN} = +3V$	2, 3	+125°C, -55°C	-	-2.5	V
Short Circuit Output	+I _{SC}	V _{IN} = ±2.5V	1	+25°C	50	-	mA
Current		V _{OUT} = 0V	2, 3	+125°C, -55°C	50	-	mA
	-I _{SC}	V _{IN} = ±2.5V	1	+25°C	-	-40	mA
		$V_{OUT} = 0V$	2, 3	+125°C, -55°C	-	-40	mA
Output Current	+I _{OUT}	Note 1	1	+25°C	20	-	mA
			2, 3	+125°C, -55°C	16.6	-	mA
	-I _{OUT}	Note 1	1	+25°C	-	-20	mA
			2, 3	+125°C, -55°C	-	-16.6	mA
Quiescent Power	I _{CC}	R _L = 400Ω	1	+25°C	-	10	mA/Op Amp
Supply Current			2, 3	+125°C, -55°C	-	10	mA/Op Amp
	I _{EE}	$R_L = 400\Omega$	1	+25°C	-10	-	mA/Op Amp
			2, 3	+125°C, -55°C	-10	-	mA/Op Amp
Transimpedance	+A _{ZOL1}	$R_L = 400\Omega$	1	+25°C	1	-	MΩ
		$V_{OUT} = \pm 2.5 V$	2, 3	+125°C	0.5	-	MΩ
		$V_{OUT} = \pm 2.25 V$	3	-55°C	0.5	-	MΩ
	-A _{ZOL1}	$R_L = 400\Omega$	1	+25°C	1	-	MΩ
		$V_{OUT} = \pm 2.5 V$	2, 3	+125°C	0.5	-	MΩ
		V _{OUT} = ±2.25V	3	-55°C	0.5	-	MΩ

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_{SOURCE} = 0\Omega$, $R_L = 400\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

NOTE:

1. Guaranteed from V_{OUT} Test with R_L = 150 $\Omega,$ by: I_{OUT} = $V_{OUT}/150\Omega.$

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

Table 2 Intentionally Left Blank.

					LIN	NITS	
PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	МАХ	UNITS
-3dB Bandwidth	BW(+1)	$A_V = +1, R_F = 1K$ $V_{OUT} = 100mV_{RMS}$	1	+125°C, -55°C	62	-	MHz
	BW(+2)	$A_V = +2,$ $V_{OUT} = 100mV_{RMS}$	1	+125°C, -55°C	62	-	MHz
Gain Flatness	GF5	$A_V = +2, f \le 5MHz$ $V_{OUT} = 100mV_{RMS}$	1	+125°C, -55°C	-	±0.045	dB
	GF10	A_V = +2, f ≤10MHz V _{OUT} = 100mV _{RMS}	1	+125°C, -55°C	-	±0.085	dB
	GF20	$A_V = +2, f \le 20MHz$ $V_{OUT} = 100mV_{RMS}$	1	+125°C, -55°C	-	±0.65	dB
Slew Rate	+SR(+1)	$A_V = +1, R_F = 1K$ $V_{OUT} = -2V$ to $+2V$	1, 4	+125°C, -55°C	250	-	V/µs
	-SR(+1)	$A_V = +1, R_F = 1K$ $V_{OUT} = +2V$ to -2V	1, 4	+125°C, -55°C	240	-	V/µs
	+SR(+2)	$A_V = +2$, $V_{OUT} = -2V$ to $+2V$	1, 4	+125°C, -55°C	400	-	V/µs
	-SR(+2)	$A_V = +2, V_{OUT} = +2V \text{ to } -2V$	1, 4	+125°C, -55°C	360	-	V/µs
Rise and Fall Time	Τ _R	$A_V = +2, V_{OUT} = -0.5V$ to +0.5V	1, 2	+125°C, -55°C	-	6.5	ns
	Τ _F	$A_V = +2, V_{OUT} = +0.5V$ to -0.5V	1, 2	+125°C, -55°C	-	6.5	ns
Overshoot	+OS	$A_V = +2, V_{OUT} = -0.5V \text{ to } +0.5V$	1, 3	+125°C, -55°C	-	35	%
	-OS	$A_V = +2, V_{OUT} = +0.5V$ to -0.5V	1, 3	+125°C, -55°C	-	27	%
Propagation Delay	+T _P	$A_V = +2, R_F = 681\Omega$ $V_{OUT} = 0V \text{ to } 1V$	1, 2	+125°C, -55°C	-	9.5	ns
	-T _P	$A_V = +2, R_F = 681\Omega$ $V_{OUT} = 1V \text{ to } 0V$	1, 2	+125°C, -55°C	-	9.0	ns

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: $V_{SUPPLY} = \pm 5V$, $A_V = +2$, $R_F = 681\Omega$, $R_L = 400\Omega$, Unless Otherwise Specified

NOTES:

1. Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot-to-lot and within lot variation.

2. Measured between 10% and 90% points.

- 3. For 200ps input transition times. Overshoot decreases as input transition times increase, especially for A_V = +1. Please refer to Performance Curves.
- 4. Measured between 25% and 75% points.

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLE 1)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1 (Note 1), 2, 3, 4
Group A Test Requirements	1, 2, 3, 4
Groups C and D Endpoints	1

NOTE:

1. PDA applies to Subgroup 1 only.



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 $V_{+} = +5.5V \pm 0.5V$ $V_{-} = -5.5V \pm 0.5V$

Die Characteristics

DIE DIMENSIONS:

 $65 \ x \ 100 \ x \ 19 \ mils \pm 1 \ mils$ $1650 \ x \ 2540 \ x \ 483 \mu m \pm 25.4 \mu m$

METALLIZATION:

Type: Metal 1: AlCu (1%), Metal 2: AlCu (1%) Thickness: Metal 1: 8kÅ \pm 0.4kÅ, Metal 2: 16kÅ \pm 0.8kÅ

WORST CASE CURRENT DENSITY:

 $1.9 \times 10^5 \text{ A/cm}^2 \text{ at } 15 \text{mA}$

SUBSTRATE POTENTIAL (Powered Up): V-

GLASSIVATION:

Type: Nitride Thickness: $4k\dot{A} \pm 0.4k\dot{A}$

TRANSISTOR COUNT: 124

PROCESS: Bipolar Dielectric Isolation

Metallization Mask Layout





Ceramic Dual-In-Line Frit Seal Packages (CerDIP)



NOTES:

- 1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
- 2. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
- 3. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness.
- Corner leads (1, N, N/2, and N/2+1) may be configured with a partial lead paddle. For this configuration dimension b3 replaces dimension b2.
- 5. This dimension allows for off-center lid, meniscus, and glass overrun.
- 6. Dimension Q shall be measured from the seating plane to the base plane.
- 7. Measure dimension S1 at all four corners.
- 8. N is the maximum number of terminal positions.
- 9. Dimensioning and tolerancing per ANSI Y14.5M 1982.
- 10. Controlling dimension: INCH.

F8.3A MIL-STD-1835 GDIP1-T8 (D-4, CONFIGURATION A) 8 LEAD CERAMIC DUAL-IN-LINE FRIT SEAL PACKAGE

	INCHES		MILLIM		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
А	-	0.200	-	5.08	-
b	0.014	0.026	0.36	0.66	2
b1	0.014	0.023	0.36	0.58	3
b2	0.045	0.065	1.14	1.65	-
b3	0.023	0.045	0.58	1.14	4
с	0.008	0.018	0.20	0.46	2
c1	0.008	0.015	0.20	0.38	3
D	-	0.405	-	10.29	5
E	0.220	0.310	5.59	7.87	5
е	0.100	BSC	2.54 BSC		-
eA	0.300	BSC	7.62 BSC		-
eA/2	0.150	0.150 BSC		3.81 BSC	
L	0.125	0.200	3.18	5.08	-
Q	0.015	0.060	0.38	1.52	6
S1	0.005	-	0.13	-	7
α	90 ⁰	105 ⁰	90 ⁰	105 ⁰	-
aaa	-	0.015	-	0.38	-
bbb	-	0.030	-	0.76	-
ccc	-	0.010	-	0.25	-
М	-	0.0015	-	0.038	2, 3
N	8	3	8		8

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DESIGN INFORMATION

HA5023

January 1995

Dual 125MHz Video Current Feedback Amplifier

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Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$, Unless Otherwise Specified.



FIGURE 1. NON-INVERTING FREQENCY RESPONSE



FIGURE 3. PHASE RESPONSE AS A FUNCTION OF FREQUENCY



FIGURE 2. INVERTING FREQUENCY RESPONSE



FIGURE 4. BANDWIDTH AND GAIN PEAKING vs FEEDBACK RESISTANCE

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Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}$ C, Unless Otherwise Specified. (Continued)







FIGURE 7. BANDWIDTH vs FEEDBACK RESISTANCE









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Typical Performance Curves $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_F = 1k\Omega$, $R_L = 400\Omega$, $T_A = 25^{\circ}C$, Unless Otherwise Specified. (Continued)



FIGURE 9. DIFFERENTIAL GAIN vs SUPPLY VOLTAGE



FIGURE 11. DISTORTION vs FREQUENCY





FIGURE 10. DIFFERENTIAL PHASE vs SUPPLY VOLTAGE







FIGURE 14. PROPAGATION DELAY vs SUPPLY VOLTAGE

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FIGURE 19. INPUT OFFSET VOLTAGE vs TEMPERATURE

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HA5023





FIGURE 31. DISABLE FEEDTHROUGH vs FREQUENCY





FIGURE 33. TRANSIMPEDENCE vs FREQUENCY

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Application Information

Optimum Feedback Resistor

The plots of inverting and non-inverting frequency response, see Figure 1 and Figure 2 in the typical performance section, illustrate the performance of the HA5023 in various closed loop gain configurations. Although the bandwidth dependency on closed loop gain isn't as severe as that of a voltage feedback amplifier, there can be an appreciable decrease in bandwidth at higher gains. This decrease may be minimized by taking advantage of the current feedback amplifier's unique relationship between bandwidth and R_F. All current feedback amplifiers require a feedback resistor, even for unity gain applications, and R_F, in conjunction with the internal compensation capacitor, sets the dominant pole of the frequency response. Thus, the amplifier's bandwidth is inversely proportional to R_F. The HA5023 design is optimized for a 1000 Ω R_F at a gain of +1. Decreasing R_F in a unity gain application decreases stability, resulting in excessive peaking and overshoot. At higher gains the amplifier is more stable, so R_F can be decreased in a trade-off of stability for bandwidth.

The table below lists recommended R_F values for various gains, and the expected bandwidth.

GAIN (A _{CL})	R_F (Ω)	BANDWIDTH (MHz)
-1	750	100
+1	1000	125
+2	681	95
+5	1000	52
+10	383	65
-10	750	22

PC Board Layout

The frequency response of this amplifier depends greatly on the amount of care taken in designing the PC board. The use of low inductance components such as chip resistors and chip capacitors is strongly recommended. If leaded components are used the leads must be kept short especially for the power supply decoupling components and those components connected to the inverting input.

Attention must be given to decoupling the power supplies. A large value ($10\mu F$) tantalum or electrolytic capacitor in parallel with a small value ($0.1\mu F$) chip capacitor works well in most cases.

A ground plane is strongly recommended to control noise. Care must also be taken to minimize the capacitance to ground seen by the amplifier's inverting input (-IN). The larger this capacitance, the worse the gain peaking, resulting in pulse overshoot and possible instability. It is recommended that the ground plane be removed under traces connected to -IN, and that connections to -IN be kept as short as possible to minimize the capacitance from this node to ground.

Driving Capacitive Loads

Capacitive loads will degrade the amplifier's phase margin resulting in frequency response peaking and possible oscillations. In most cases the oscillation can be avoided by placing an isolation resistor (R) in series with the output as shown in Figure 34.



FIGURE 34. PLACEMENT OF THE OUTPUT ISOLATION RESISTOR, R

The selection criteria for the isolation resistor is highly dependent on the load, but 27Ω has been determined to be a good starting value.

Power Dissipation Considerations

Due to the high supply current inherent in dual amplifiers, care must be taken to insure that the maximum junction temperature (T_J , see Absolute Maximum Ratings) is not exceeded. Figure 35 shows the maximum ambient temperature versus supply voltage for the available package styles. It is recommended that thermal calculations, which take into account output power, be performed by the designer.



FIGURE 35. MAXIMUM OPERATING AMBIENT TEMPERATURE vs SUPPLY VOLTAGE

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Electrical Specifications	V+ = +5V, V- = -5V, R_F = 1kΩ, A_V = +1, R_L = 400Ω, C_L ≤10pF, Unless C	Otherwise Specified
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PARAMETER	(NOTE 16) TEST LEVEL	TEMPERATURE	HA5023I			
			MIN	ТҮР	МАХ	UNITS
INPUT CHARACTERISTICS	•					
Input Offset Voltage (V _{IO})	А	+25°C	-	0.8	3	mV
	А	Full	-	-	5	mV
Delta V _{IO} Between Channels	А	Full	-	1.2	3.5	mV
Average Input Offset Voltage Drift	В	Full	-	5	-	μV/ ^o C
V _{IO} Common Mode Rejection Ratio (Note 3)	А	+25°C	53	-	-	dB
	А	Full	50	-	-	dB
V _{IO} Power Supply Rejection Ratio (Note 4)	А	+25°C	60	-	-	dB
	А	Full	55	-	-	dB
Input Common Mode Range (Note 3)	А	Full	±2.5	-	-	V
Non-Inverting Input (+IN) Current	А	+25°C	-	3	8	μA
	А	Full	-	-	20	μA
+IN Common Mode Rejection (Note 3) (+I _{BCMR} = $\frac{1}{+R_{IN}}$)	А	+25°C	-	-	0.15	μ A /V
	А	Full	-	-	0.5	μ A /V
+IN Power Supply Rejection (Note 4)	А	+25°C	-	-	0.1	μ A /V
	А	Full	-	-	0.3	μ A /V
Inverting Input (-IN) Current	А	+25°C, +85°C	-	4	12	μA
	А	-40°C	-	10	30	μA
Delta - IN BIAS Current Between Channels	А	+25°C, +85°C	-	6	15	μA
	А	-40°C	-	10	30	μA
-IN Common Mode Rejection (Note 3)	А	+25°C	-	-	0.4	μ A /V
	А	Full	-	-	1.0	μ A /V
-IN Power Supply Rejection (Note 4)	А	+25°C	-	-	0.2	μ A /V
	А	Full	-	-	0.5	μ A /V
Input Noise Voltage (f = 1kHz)	В	+25°C	-	4.5	-	nV/√Hz
+Input Noise Current (f = 1kHz)	В	+25°C	-	2.5	-	pA/√Hz
-Input Noise Current (f = 1kHz)	В	+25°C	-	25.0	-	pA/√Hz
TRANSFER CHARACTERISTICS	•				1	
Transimpedence (Note 14)	А	+25°C	1.0	-	-	MΩ
	А	Full	0.85	-	-	MΩ
Open Loop DC Voltage Gain, RL = 400 Ω , V _{OUT} = ± 2.5 V	А	+25°C	70	-	-	dB
	А	Full	65	-	-	dB
Open Loop DC Voltage Gain, R _L = 100 Ω , V _{OUT} = ± 2.5 V	A	+25°C	50	-	-	dB
	А	Full	45	-	-	dB
OUTPUT CHARACTERISTICS				•	1	

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PARAMETER	(NOTE 16)	TEMPERATURE	HA5023I			
	LEVEL		MIN	ТҮР	МАХ	UNITS
Output Voltage Swing (Note 13)	А	+25°C	±2.5	±3.0	-	V
	А	Full	±2.5	±3.0	-	V
Output Current (Note 13)	В	Full	±16.6	±20.0	-	mA
Output Current (Short Circuit, Note 10)	А	Full	±40	±60	-	mA
POWER SUPPLY CHARACTERISTICS				•		
Supply Voltage Range	А	+25°C	5	-	15	V
Quiescent Supply Current	A	Full	-	7.5	10	mA/Op Amp
AC CHARACTERISTICS ($A_V = +1$)				•		
Slew Rate (Note 5)	В	+25°C	275	350	-	V/µs
Full Power Bandwidth (Note 6)	В	+25°C	22	28	-	MHz
Rise Time (Note 7)	В	+25°C	-	6	-	ns
Fall Time (Note 7)	В	+25°C	-	6	-	ns
Propagation Delay (Note 7)	В	+25°C	-	6	-	ns
Overshoot	В	+25°C	-	4.5	-	%
-3dB Bandwidth (Note 8)	В	+25°C	-	125	-	MHz
Settling Time to 1%, 2V Output Step	В	+25°C	-	50	-	ns
Settling Time to 0.25%, 2V Output Step	В	+25°C	-	75	-	ns
AC CHARACTERISTICS ($A_V = +2, R_F = 681\Omega$)						
Slew Rate (Note 5)	В	+25°C	-	475	-	V/µs
Full Power Bandwidth (Note 6)	В	+25°C	-	26	-	MHz
Rise Time (Note 7)	В	+25°C	-	6	-	ns
Fall Time (Note 7)	В	+25°C	-	6	-	ns
Propagation Delay (Note 7)	В	+25°C	-	6	-	ns
Overshoot	В	+25°C	-	12	-	%
-3dB Bandwidth (Note 8)	В	+25°C	-	95	-	MHz
Settling Time to 1%, 2V Output Step	В	+25°C	-	50	-	ns
Settling Time to 0.25%, 2V Output Step	В	+25°C	-	100	-	ns
Gain Flatness 5MHz	В	+25°C	-	0.02	-	dB
20MH	z B	+25°C	-	0.07	-	dB
AC CHARACTERISTICS (A _V = +10, R _F = 383Ω)						
Slew Rate (Note 5)	В	+25°C	350	475	-	V/µs
Full Power Bandwidth (Note 6)	В	+25°C	28	38	-	MHz
Rise Time (Note 7)	В	+25°C	-	8	-	ns
Fall Time (Note 7)	В	+25°C	-	9	-	ns
Propagation Delay (Note 7)	В	+25°C	-	9	-	ns

	(NOTE 16)		HA5023I			
PARAMETER	LEVEL	TEMPERATURE	MIN	ТҮР	МАХ	UNITS
Overshoot	В	+25°C	-	1.8	-	%
-3dB Bandwidth (Note 8)	В	+25°C	-	65	-	MHz
Settling Time to 1%, 2V Output Step	В	+25°C	-	75	-	ns
Settling Time to 0.1%, 2V Output Step	В	+25°C	-	130	-	ns
VIDEO CHARACTERISTICS						
Differential Gain (Notes 11, 13)	В	+25°C	-	0.03	-	%
Differential Phase (Notes 11, 13)	В	+25°C	-	0.03	-	Degrees

Electrical Specifications V + = +5V, V - = -5V, $R_F = 1k\Omega$, $A_V = +1$, $R_L = 400\Omega$, $C_L \le 10pF$, Unless Otherwise Specified (Contin-

NOTES:

1. Absolute maximum ratings are limiting values, applied individually, beyond which the serviceability of the circuit may be impaired. Functional operation under any of these conditions is not necessarily implied.

2. Output is protected for short circuits to ground. Brief short circuits to ground will not degrade reliability, however, continuous (100% duty cycle) output current should not exceed 15mA for maximum reliability.

3. $V_{CM} = \pm 2.5V$. At -40°C Product is tested at $V_{CM} = \pm 2.25V$ because Short Test Duration does not allow self heating.

4. $\pm 3.5V \le V_S \le \pm 6.5V$

5. V_{OUT} switches from -2V to +2V, or from +2V to -2V. Specification is from the 25% to 75% points.

6. FPBW = $\frac{\text{Slew Rate}}{2\pi V_{\text{PEAK}}}$; $V_{\text{PEAK}} = 2V$

7. R_L = 100Ω, V_{OUT} = 1V. Measured from 10% to 90% points for rise/fall times; from 50% points of input and output for propagation delay.

8. $R_L = 400\Omega$, $V_{OUT} = 100mV$.

9. A. Production Tested; B. Guaranteed Limit or Typical based on characterization; C. Design Typical for information only.

- 10. $V_{IN} = \pm 2.5V$, $V_{OUT} = 0V$.
- 11. Measured with a VM700A video tester using an NTC-7 composite VITS.
- 12. Maximum power dissipation, including output load, must be designed to maintain junction temperature below +175°C for die, and below +150°C for plastic packages. See Applications Information section for safe operating area information.

13. $\mathsf{R}_\mathsf{L} = 150 \Omega$.

- 14. V_{OUT} = ±2.5V. At -40°C Product is tested at V_{OUT} = ±2.25V because Short Test Duration does not allow self heating.
- 15. ESD protection is for human body model tested per MIL-STD 883, Method 3015.7.
- 16. A. Production Tested; B. Guaranteed limit or Typical based on characterization; C. Design Typical for information only.

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